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(54) **MAGNETIC CORE INDUCTOR
SEMICONDUCTOR STRUCTURE AND
METHOD**

(71) Applicant: **Taiwan Semiconductor
Manufacturing Company, Ltd.,
Hsinchu (TW)**

(72) Inventors: **Wei-Li Huang**, Pingtung (TW);
Chi-Cheng Chen, Tainan (TW);
Hon-Lin Huang, Hsinchu (TW);
Chien-Chih Chou, New Taipei (TW);
Chin-Yu Ku, Hsinchu (TW);
Chen-Shien Chen, Zhubei (TW)

(73) Assignee: **Taiwan Semiconductor
Manufacturing Company, Ltd.,
Hsinchu (TW)**

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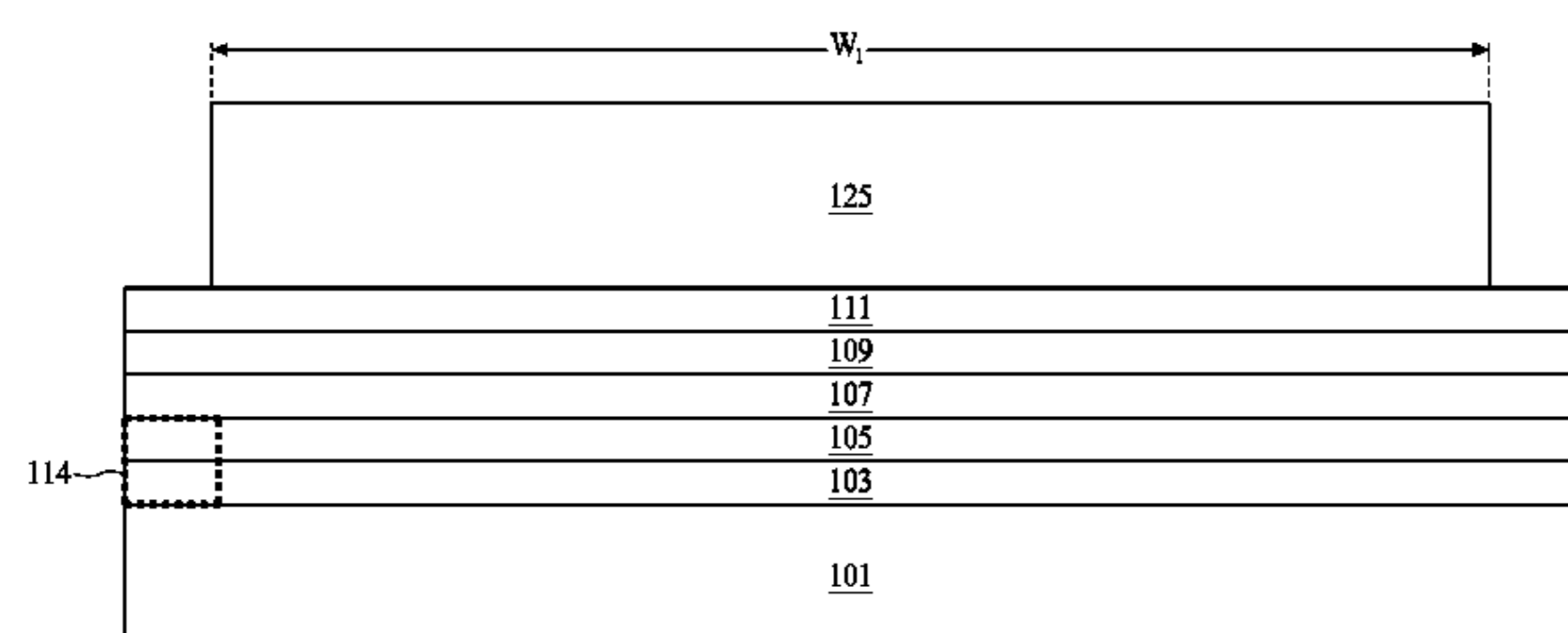
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Primary Examiner — Mary A Wilczewski

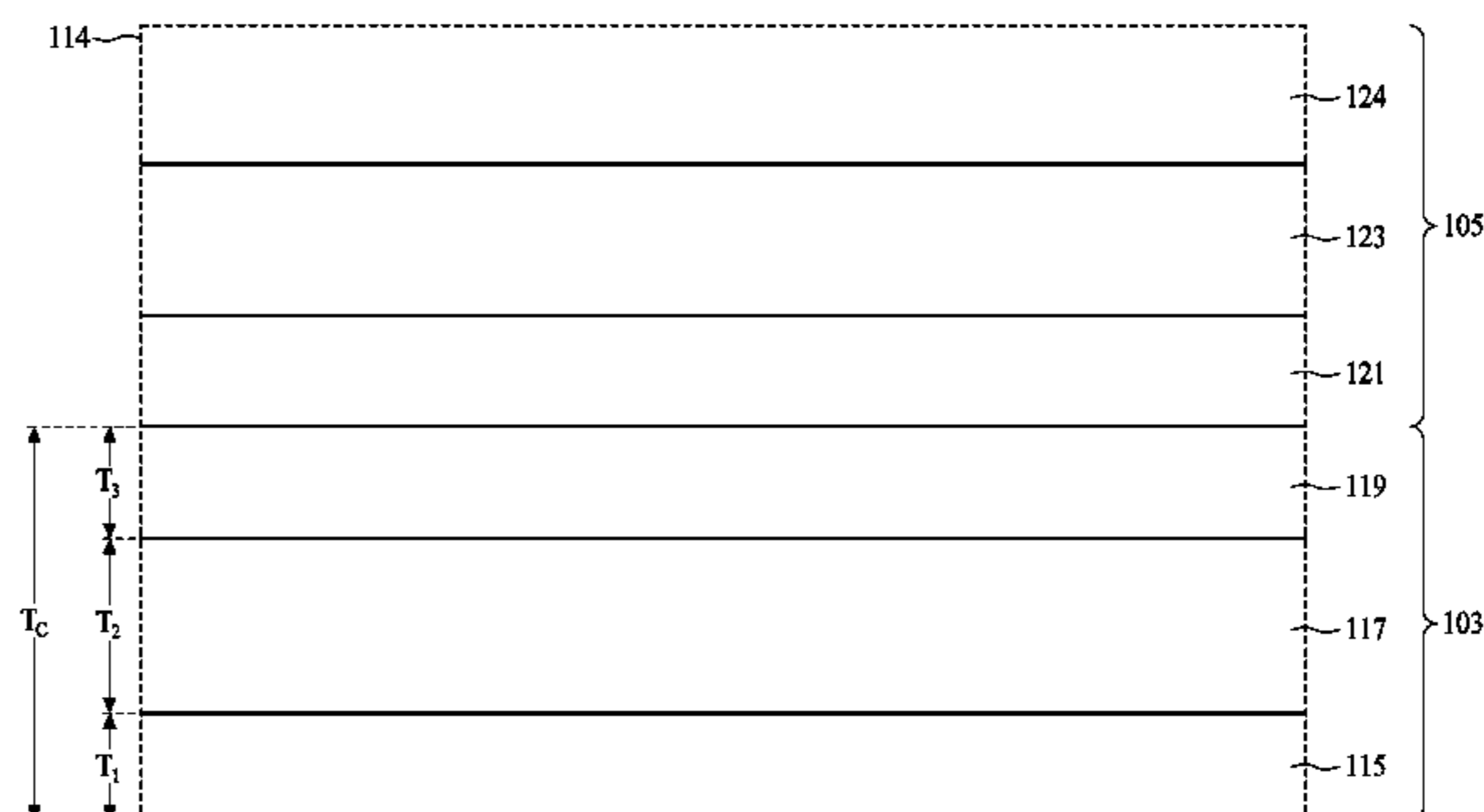
Assistant Examiner — Tsz K Chiu

(74) *Attorney, Agent, or Firm* — Slater Matsil, LLP

(57) **ABSTRACT**

A method of manufacturing a semiconductor device and the
semiconductor device are provided in which a plurality of
layers with cobalt-zirconium-tantalum are formed over a
semiconductor substrate, the plurality of layers are pat-
terned, and multiple dielectric layers and conductive mate-
rials are deposited over the CZT material. Another layer of
CZT material encapsulates the conductive material.

20 Claims, 9 Drawing Sheets



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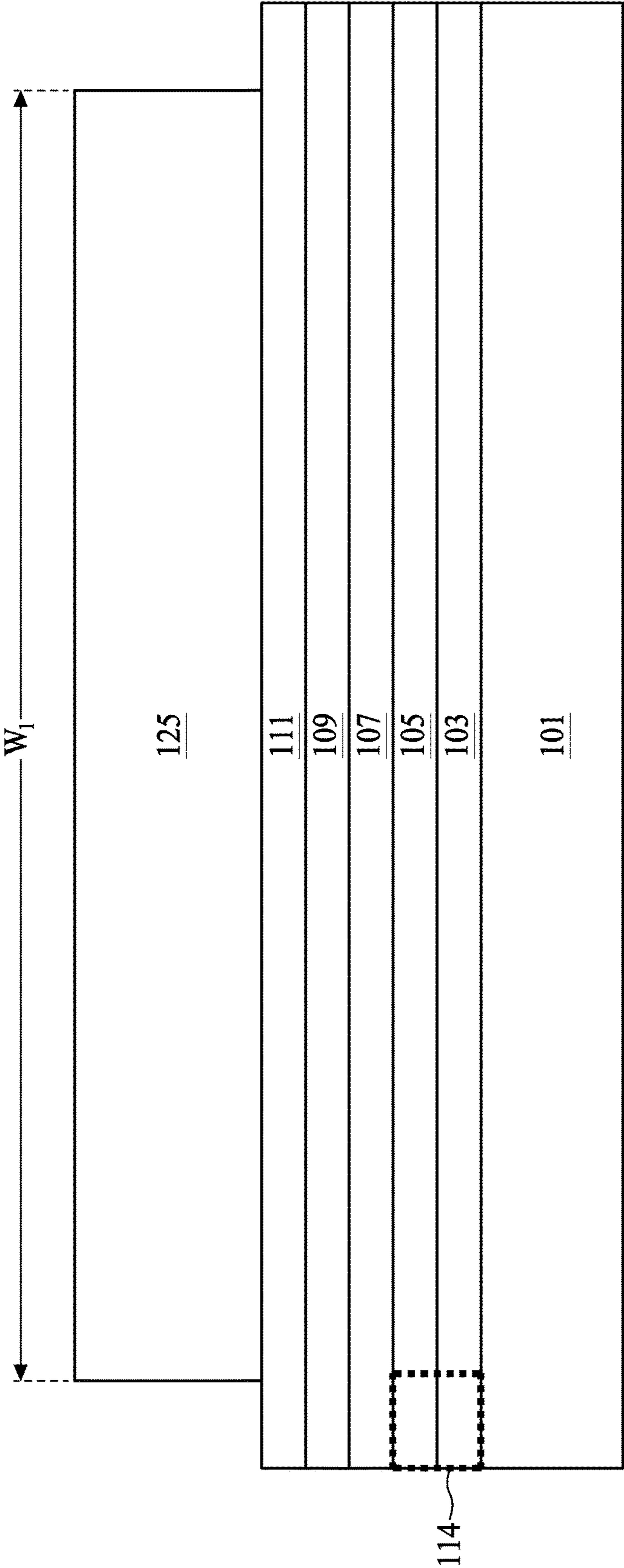


Figure 1A

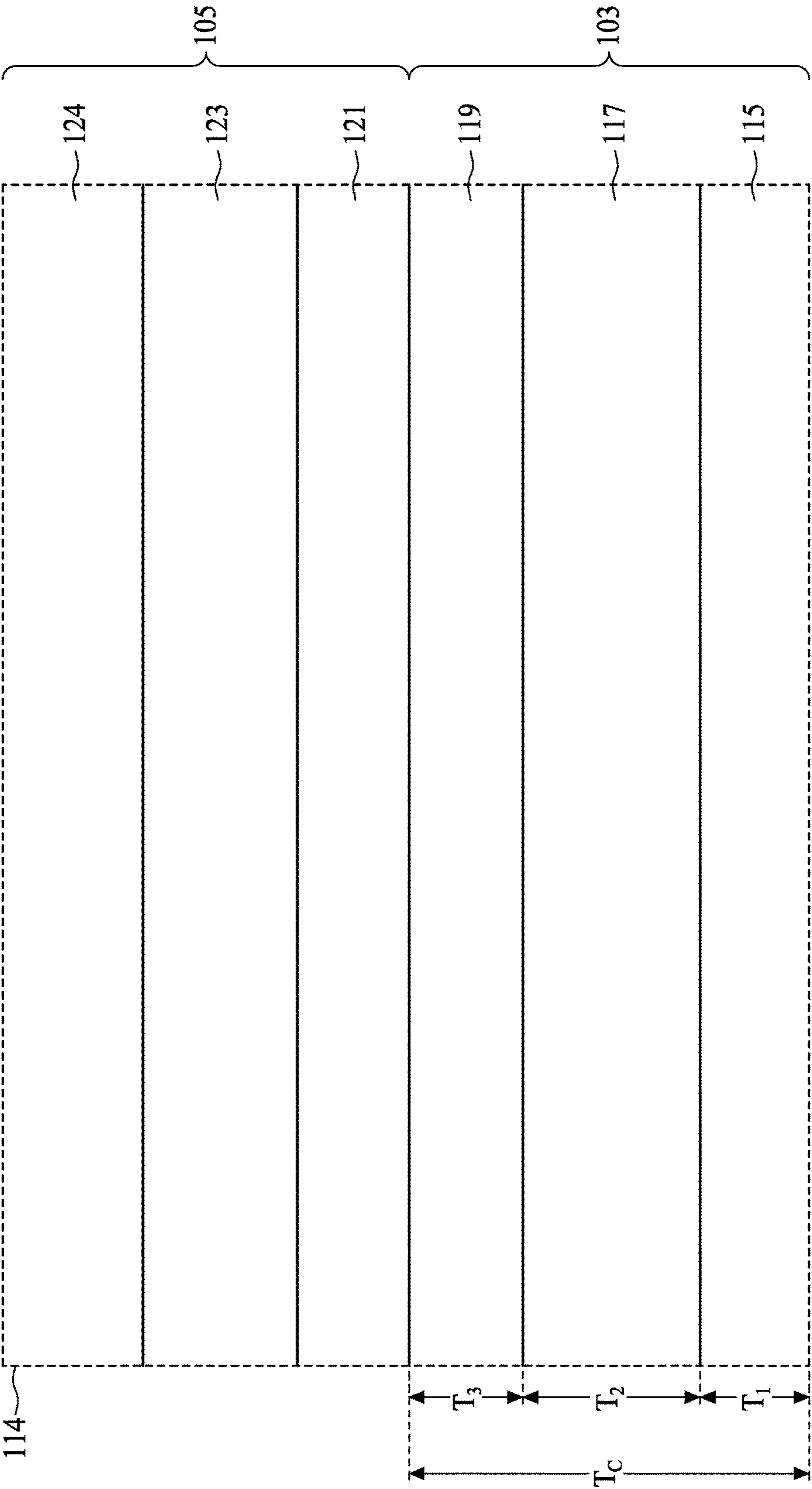


Figure 1B

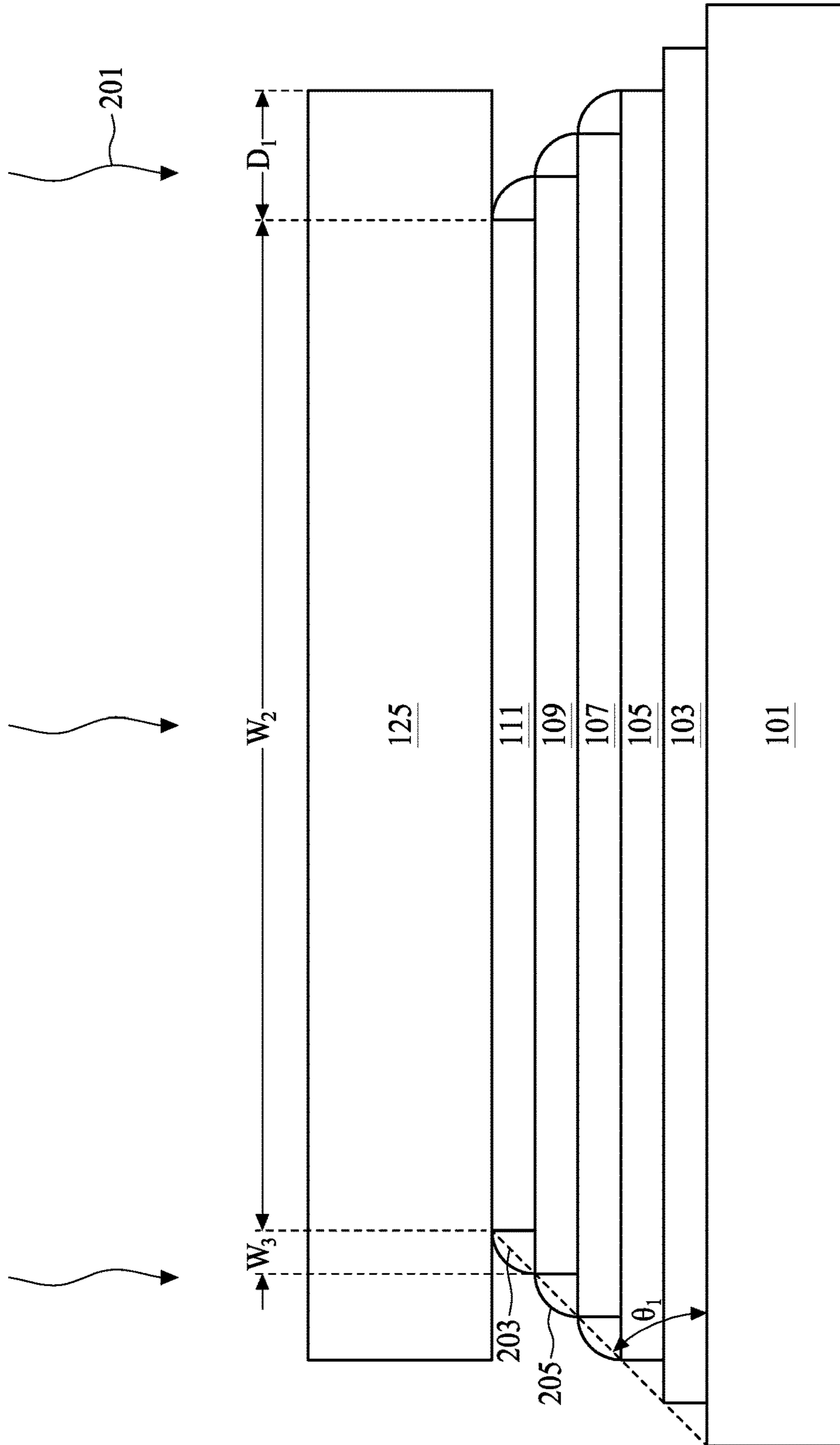


Figure 2

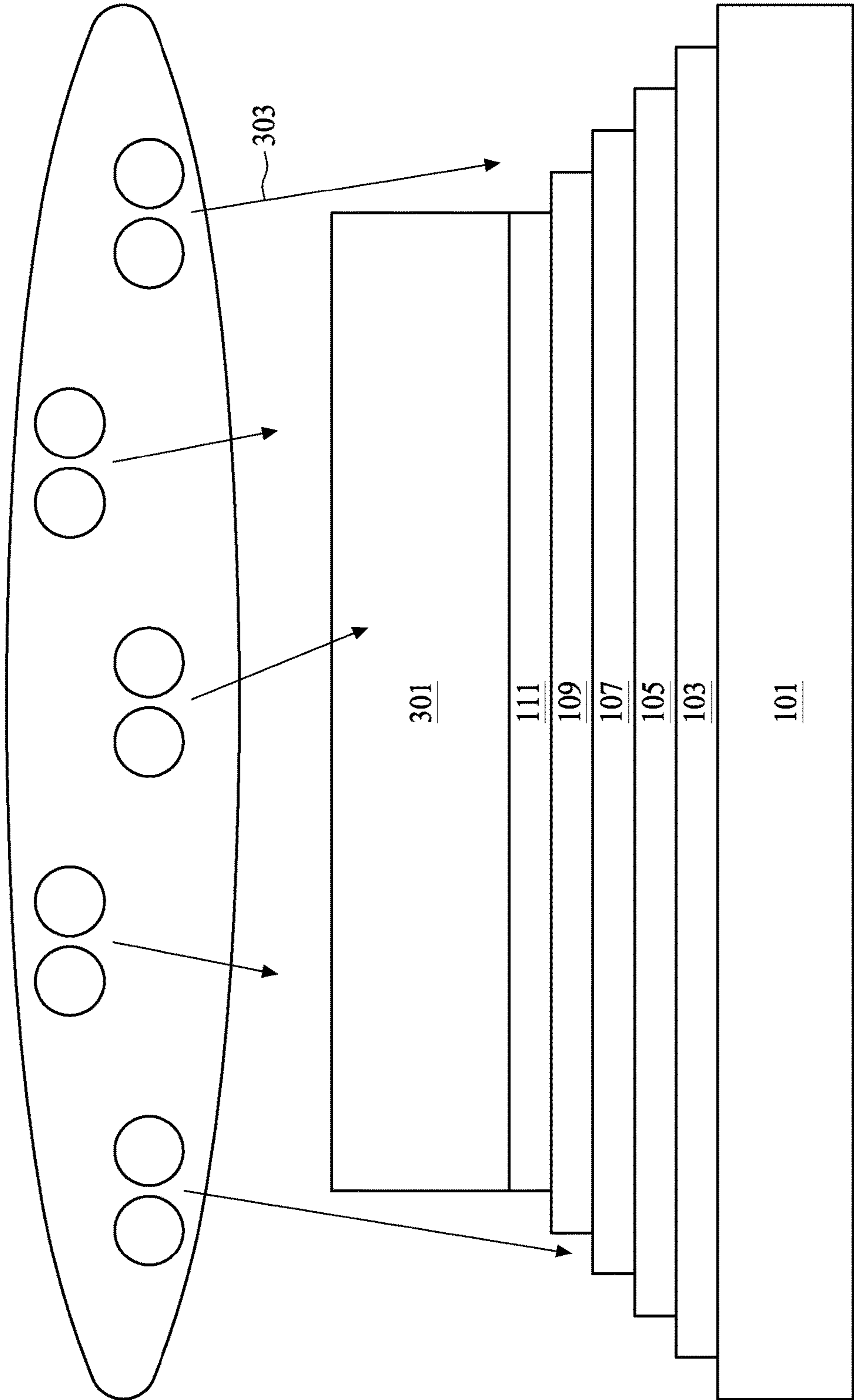


Figure 3

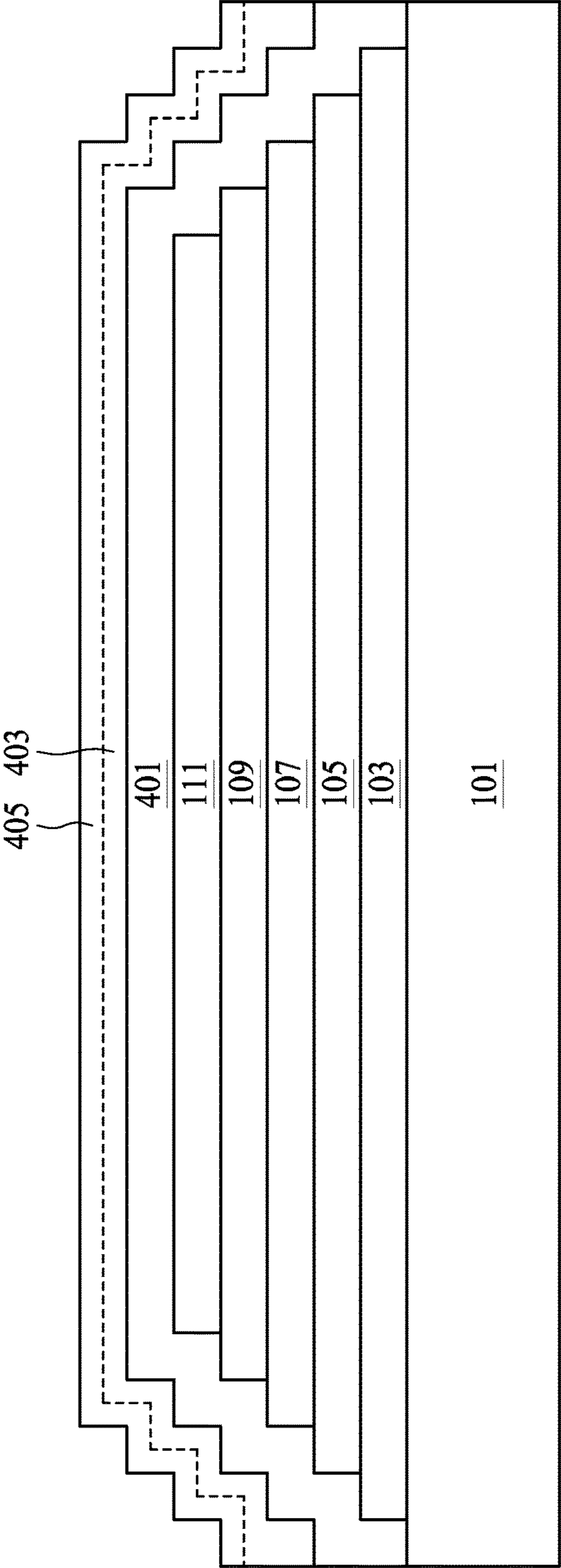


Figure 4

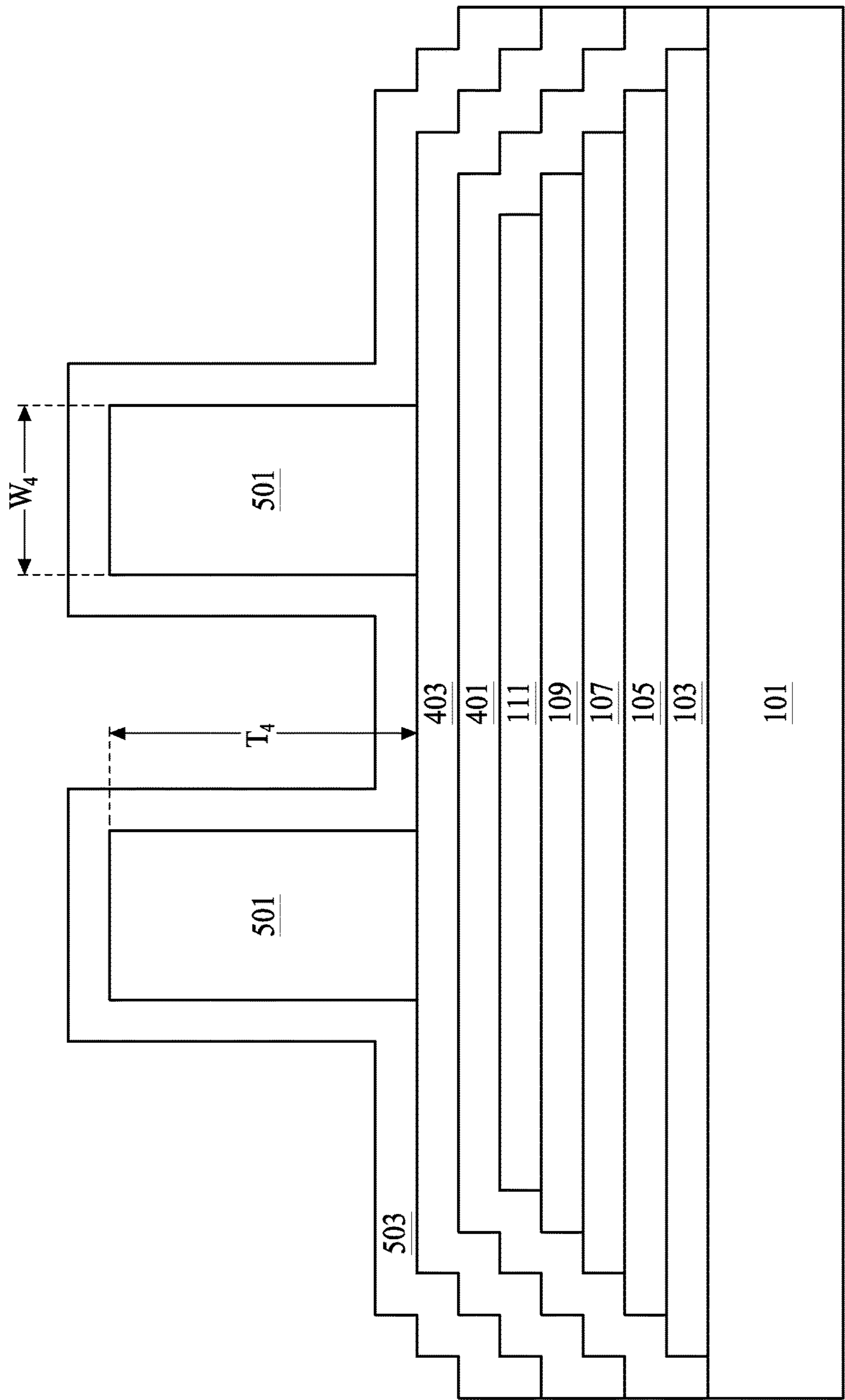


Figure 5

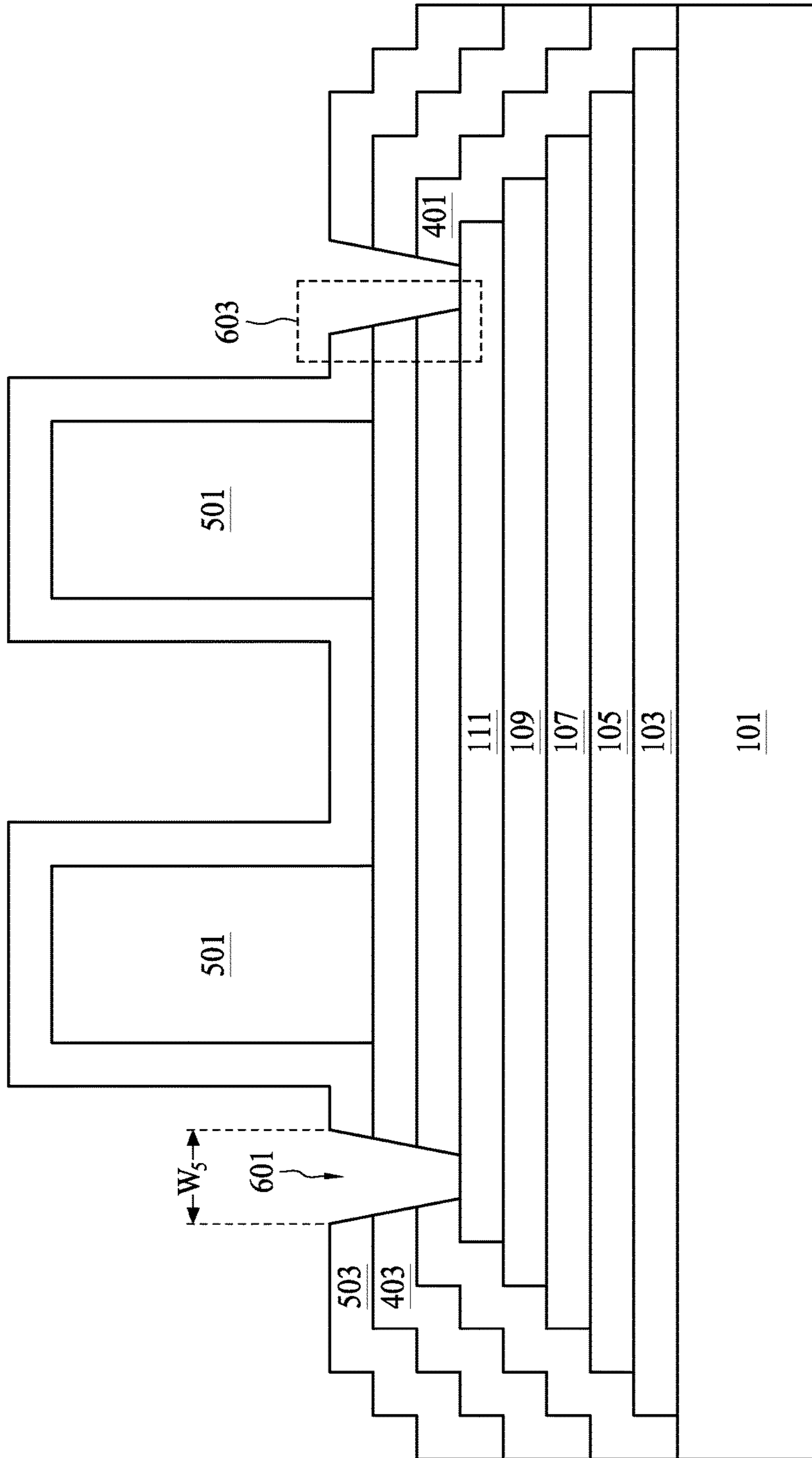


Figure 6A

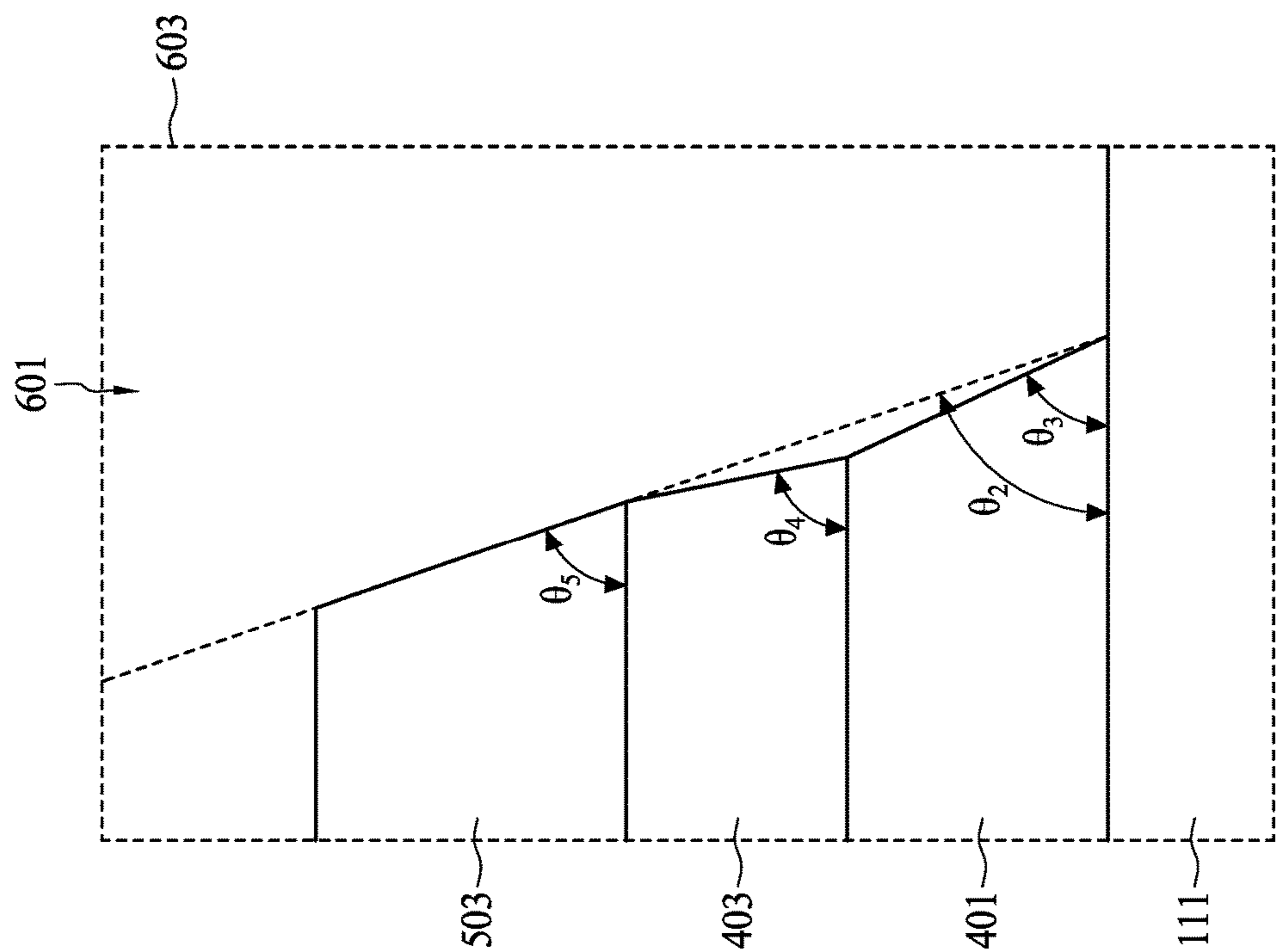


Figure 6B

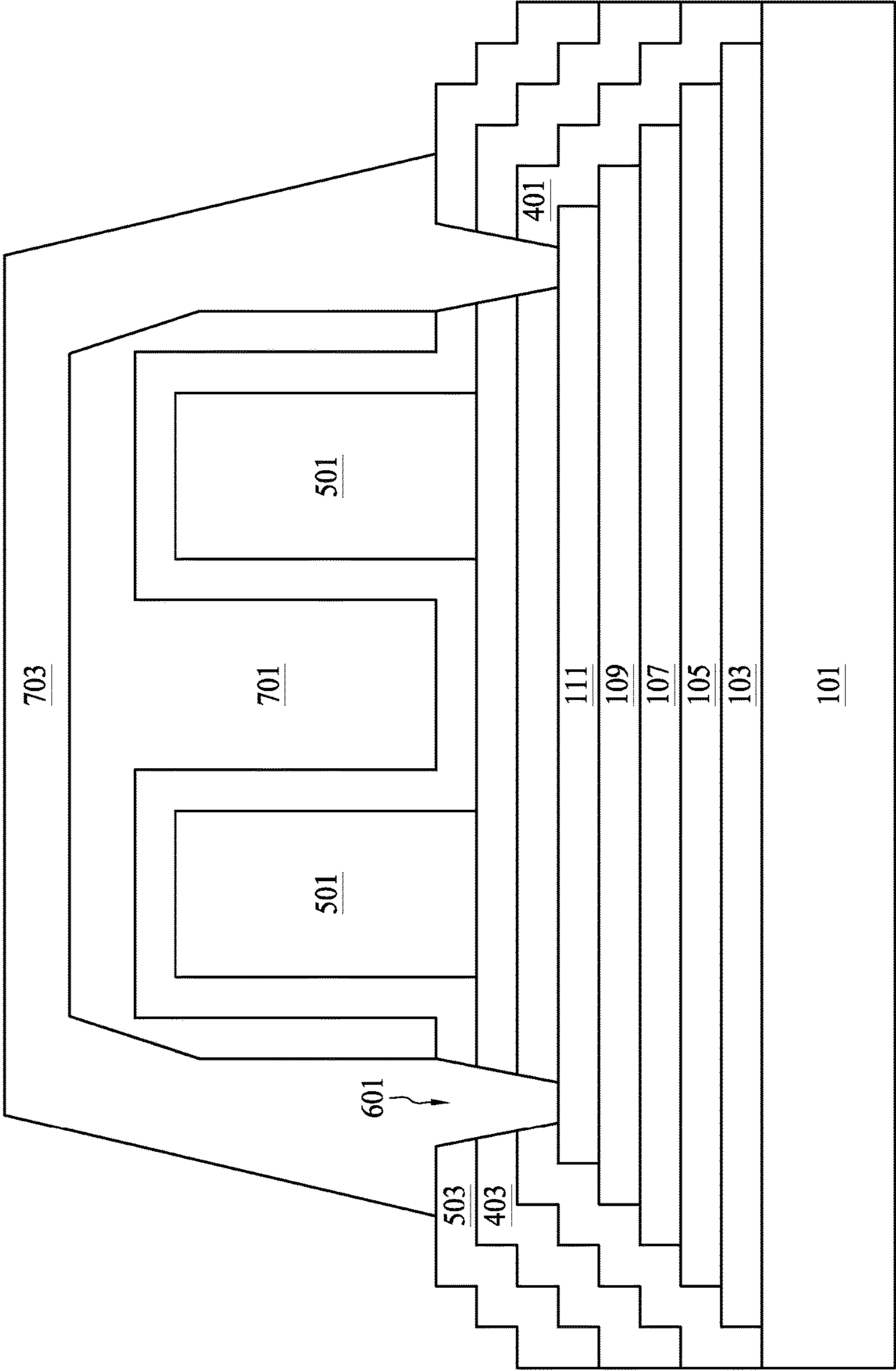


Figure 7

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MAGNETIC CORE INDUCTOR SEMICONDUCTOR STRUCTURE AND METHOD

This application is a division of and claims the benefit of U.S. patent application Ser. No. 15/582,963, filed on May 1, 2017, entitled "Semiconductor Structure and Method," which application claims the benefit of U.S. Provisional Application Ser. No. 62/446,155, filed on Jan. 13, 2017, entitled "Semiconductor Structure and Method," which applications are hereby incorporated herein by reference.

BACKGROUND

Generally, an inductor is a passive electrical component that can store energy in a magnetic field created by an electric current passing through it. An inductor may be constructed as a coil of conductive material wrapped around a core of dielectric or magnetic material. One parameter of an inductor that may be measured is the inductor's ability to store magnetic energy, also known as the inductor's inductance. Another parameter that may be measured is the inductor's Quality (Q) factor. The Q factor of an inductor is a measure of the inductor's efficiency and may be calculated as the ratio of the inductor's inductive reactance to the inductor's resistance at a given frequency.

Inductors may be utilized in a wide variety of applications. One such application of an inductor may be as a choke, in which an inductor is designed to have a high inductive reactance to, or block, signals with certain frequencies in an electrical circuit while allowing passage of other signals at different frequencies in the electrical circuit. A choke may be made, for example to block a radio frequency (RF), and may be called a RF choke, which is of use in radio communications. Another application of an inductor may be as a voltage regulator, in which an inductor is used in a voltage control circuit to reduce sudden changes in the power supply, thus providing a smooth voltage supply to electrical systems for improved system performance.

Traditionally, inductors are used as discrete components which are placed on a substrate such as a printed circuit board (PCB) and connected to other parts of the system, such as an integrated circuit (IC) chip, via contact pads and conductive traces. Discrete inductors are bulky, use larger footprints on the PCB, and consume lots of power. Due to the continued miniaturization of electric devices, it is desirable to integrate inductors into IC chips. Therefore, there is a need for manufacturing integrated inductors that provide the benefit of size, cost and power reduction without sacrificing the electrical performance.

BRIEF DESCRIPTION OF THE DRAWINGS

Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

FIGS. 1A-1B illustrate CZT multilayers formed over a semiconductor substrate in accordance with some embodiments.

FIG. 2 illustrates a patterning of the CZT multilayers in accordance with some embodiments.

FIG. 3 illustrates a treatment in accordance with some embodiments.

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FIG. 4 illustrates formation of dielectric caps in accordance with some embodiments.

FIG. 5 illustrates formation of inductor coils in accordance with some embodiments.

FIGS. 6A-6B illustrate formation of openings through dielectric caps in accordance with some embodiments.

FIG. 7 illustrates formation of a CZT multilayer over the inductor coils in accordance with an embodiment.

DETAILED DESCRIPTION

The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

Further, spatially relative terms, such as "beneath," "below," "lower," "above," "upper" and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

Embodiments will be described with respect to cobalt-zirconium-tantalum (CZT) materials integrated as part of an inductor. Other embodiments using CZT materials, however, are fully intended to be included within the scope of the embodiments.

With reference now to FIG. 1A, a first CZT multilayer **103**, a second CZT multilayer **105**, a third CZT multilayer **107**, a fourth CZT multilayer **109**, and a fifth CZT multilayer **111** are formed on a semiconductor substrate **101**. In an embodiment, the semiconductor substrate **101** may comprise bulk silicon, doped or undoped, or an active layer of a silicon-on-insulator (SOI) substrate. Generally, an SOI substrate comprises a layer of a semiconductor material such as silicon, germanium, silicon germanium, SOI, silicon germanium on insulator (SGOI), or combinations thereof. Other substrates that may be used include multi-layered substrates, gradient substrates, or hybrid orientation substrates.

Optionally, active devices (not separately illustrated) and passive devices may be formed within and/or on the semiconductor substrate **101**. Such active devices may include transistors, capacitors, resistors, combinations or these, or the like. Any suitable devices may be included.

FIG. 1B illustrates a close-up view of the dashed box labeled **114** in FIG. 1A in which the first CZT multilayer **103** and the second CZT multilayer **105** are formed over the semiconductor substrate **101**. In an embodiment the first CZT multilayer **103** is formed of a plurality of different layers, wherein at least one of the plurality of different layers

is a first CZT layer **117**. In a particular embodiment, the first CZT multilayer **103** comprises a first metal layer **115**, the first CZT layer **117**, and a first oxidized CZT (OCZT) layer **119**. The first metal layer **115**, in an embodiment, may be a metal such as tantalum, although any suitable metal may be utilized, and may be formed using a deposition process such as chemical vapor deposition, atomic layer deposition, physical vapor deposition, or any other suitable deposition process. Additionally, the first metal layer **115** may be formed to a first thickness T_1 of between about 10 Å and about 100 Å, such as about 50 Å, although any suitable thickness may be utilized.

The first CZT layer **117** is formed on the first metal layer **115** and comprises $\text{Co}_x\text{Zr}_y\text{Ta}_z$ (CZT), where x, y, and z represent the atomic percentage of cobalt (Co), zirconium (Zr), and tantalum (Ta), respectively. In some embodiments, x is in a range from about 0.85 to about 0.95, y is in a range from about 0.025 to about 0.075, and z is in a range from about 0.025 to about 0.075. In a particular embodiment, $x=0.915$, $y=0.04$, and $z=0.045$. In an embodiment the first CZT layer **117** may be formed using a deposition process such as chemical vapor deposition, atomic layer deposition, or physical vapor deposition, to a second thickness T_2 of between about 10 times and about 200 times the first thickness T_1 (of the first metal layer **115**), such as between about 100 Å and about 20000 Å, such as about 5000 Å. However, any suitable thickness or deposition process may be utilized.

The first oxidized CZT layer **119** may be formed over the first CZT layer **117** and comprises $\text{O}_v\text{Co}_x\text{Zr}_y\text{Ta}_z$ (CZT), where v, x, y, and z represent the atomic percentage of oxygen (O), cobalt (Co), zirconium (Zr), and tantalum (Ta), respectively. In some embodiments, V is in a range from about 0.5 and about 0.65, x is in a range from about 0.85 to about 0.95, y is in a range from about 0.025 to about 0.075, and z is in a range from about 0.025 to about 0.075. In a particular embodiment, $v=0.60$, $x=0.37$, $y=0.014$, and $z=0.016$. In an embodiment the first oxidized CZT layer **119** may be formed using a deposition process such as chemical vapor deposition, atomic layer deposition, or physical vapor deposition, to a third thickness T_3 of between about 1 time and about 10 times the first thickness T_1 (of the first metal layer **115**), such as between about 20 Å and about 500 Å, such as about 150 Å. However, any suitable thickness or deposition process may be utilized.

Once the first oxidized CZT layer **119** has been formed, the first CZT layer **117** may have a combined thickness between the first metal layer **115**, the first CZT layer **117**, and the first OCZT layer **119**. In an embodiment the combined thickness T_c is between about 0.1 μm and about 0.7 μm, such as about 0.5 μm. However, any suitable thickness may be utilized.

Additionally, by forming the first oxidized CZT layer **119** and the combined thickness T_c has been met, a first cycle of forming the first CZT multilayer **103** has been created. Once the first CZT multilayer **103** has been formed, the second CZT multilayer **105** may be formed by repeating the processes used to form the first CZT multilayer **103**. For example, in an embodiment the second CZT multilayer **105** may be formed by forming a second metal layer **121**, a second CZT layer **123**, and a second OCZT layer **124**, wherein the second metal layer **121**, the second CZT layer **123**, and the second OCZT layer **124** are formed from similar materials, similar processes, and similar thicknesses as the first metal layer **115**, the first CZT layer **117** and the first OCZT layer **119** in the first CZT multilayer **103**.

However, any suitable combination of materials, processes, and thicknesses may be utilized.

Returning now to FIG. 1A, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111** are formed over the second CZT multilayer **105** using a repetition of similar processes as those used for the first CZT multilayer **103** and the second CZT multilayer **105**. However, while similar processes may be used, the materials, thicknesses and processes may also be different from layer to layer. Any suitable processes and parameters may be utilized.

Additionally, while only five CZT multilayers (the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111**) are illustrated in FIG. 1A, any suitable number of CZT multilayers may be utilized. For example, in a particular embodiment there may be between about 5 and about 50 CZT multilayers, such as between about 10 and 50 CZT multilayers, such as 23 CZT multilayers. As such, the total thickness of the CZT multilayers may be between about 2 μm and about 10 μm. However, any suitable number of CZT multilayers may be utilized.

FIG. 1A additionally illustrates a placement and patterning of a first masking layer **125** over the fifth CZT multilayer **111**. In an embodiment the first masking layer **125** may be a photosensitive material placed onto the semiconductor substrate **101** using, e.g., a spin on process and then exposed to a patterned light source in order to induce a chemical reaction within the exposed portions of the photoresist. The photoresist may then be developed in order to remove either the exposed or unexposed portions of the photoresist. In another embodiment the first masking layer **125** may be a hard mask that has been patterned using a photoresist. Any suitable layer may be used to help a subsequent patterning of the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111**.

In an embodiment the first masking layer **125** is placed and patterned in order to form a mask to pattern the underlying layers (e.g., the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111**). Additionally, the first masking layer **125** may be patterned in such a way as to help shape the underlying CZT layers in a subsequent process. As such, in an embodiment the first masking layer **125** is patterned to have a first width W_1 of between about 100 μm and about 400 μm, such as about 295 μm. However, any suitable dimensions may be utilized.

FIG. 2 illustrates that, once the first masking layer **125** has been patterned, the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111** may be patterned with a first etching process (represented in FIG. 2 by wavy lines labeled **201**) using the first masking layer **125** as a mask. In an embodiment the first etching process **201** is a wet etching process using etchants that are selective to the materials of the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111**.

For example, in an embodiment the first etching process **201** may use an etchant such as Hf combined with HNO_3 , although any other suitable etchant, such as Hf or HNO_3 in an uncombined format, may alternatively be utilized. Additionally, in an embodiment in which the first etching process **201** is a wet etch, the first etching process **201** may be

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performed at a temperature of between about 20° C. and about 80° C., such as about 25° C. and for a time of between about 100 s and about 600 s, such as about 350 s. However, any suitable process parameters may be utilized.

Given the isotropic nature of the first etching process **201** in embodiments in which the first etching process **201** is a wet etching process, the individual CZT multilayers (e.g., the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111**) will be etched at different times as they are each exposed by the removal of an overlying layer. As such, the etching process will begin sooner for the CZT multilayers further away from the semiconductor substrate **101** (e.g., the fifth CZT multilayer **111**), causing one or more of the CZT multilayers to undercut the first masking layer **125**. For example, in an embodiment the CZT multilayer closest to the first masking layer **125** (e.g., the fifth CZT multilayer **111** when there are five multilayers) may undercut the first masking layer **125** by a first distance D_1 of between about 5 μm and about 50 μm , such as about 25 μm , causing the fifth CZT multilayer **111** to have a second width W_2 of between about 100 μm and about 400 μm , such as about 245 μm . However, any suitable distance may be utilized.

Additionally, the next CZT multilayer (e.g., the fourth CZT multilayer **109**) may have a first portion **203** exposed by the overlying fifth CZT multilayer **111**. In an embodiment the first portion **203** of the fourth CZT multilayer **109** may have a third width W_3 of between about 0.25 μm and about 2 μm , such as about 2 μm . However, any suitable dimensions may be utilized.

Such a structure with one CZT multilayer overlying some but not all of an underlying CZT multilayer and exposing a portion of the underlying CZT multilayer, may be repeated for each one of the CZT multilayers, causing a sidewall of the combined CZT multilayers to form a staircase pattern with a step height equal to the combined thickness T_c of the individual CZT multilayers and a step width equal to the third width W_3 . In a particular embodiment, the stair step pattern is formed with a first angle θ_1 of between about 5 and about 70 degrees, such as about 15 degrees. However, any suitable dimensions may be used.

Additionally, while the first etching process **201** forms the staircase pattern as described above, the first etching process **201** will also leave behind residue **205**. In particular, this residue **205** may be left behind on the steps of the staircase pattern and may comprise a material such as tantalum left over from the etching of the CZT material within the first CZT multilayer **103**, the second CZT multilayer **105**, the third CZT multilayer **107**, the fourth CZT multilayer **109**, and the fifth CZT multilayer **111**.

FIG. 3 illustrates a removal of the first masking layer **125**, a placement of a second masking layer **301**, and a first treatment process (represented in FIG. 2 by the arrows labeled **303**). In an embodiment in which the first masking layer **125** is a photoresist, the first masking layer **125** may be removed using an ashing process, whereby the temperature of the first masking layer **125** is increased until the photoresist experiences a thermal decomposition, whereby the remainder can thereafter be easily removed.

Once the first masking layer **125** has been removed, the second masking layer **301** may be applied in order to protect the top surface of the fifth CZT multilayer **111** during the first treatment process **303**. In an embodiment the second masking layer **301** may be similar to the first masking layer **125**, such as by being a photoresist material or a hard mask material. However, any suitable material may be utilized.

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Additionally, once the material of the second masking layer **301** has been placed, the second masking layer **301** is patterned using, e.g., an exposing and development process. In an embodiment the second masking layer **301** is patterned to cover the top surface of the fifth CZT multilayer **111** and, as such, has a similar width as the fifth CZT multilayer **111** (e.g., the second width W_2). In another embodiment the second masking layer **301** has a smaller width than the fifth CZT multilayer **111**.

Once the second masking layer **301** has been placed and patterned, the first treatment process **303** may be utilized in order to remove the tantalum residue **205** left over from the first etching process **201**. If left in place, the tantalum residue **205** will interfere with subsequent deposition processes (such as a deposition of a first dielectric cap **401** discussed below with respect to FIG. 4). As such, the first treatment process **303** is utilized to remove the tantalum residue **205** so that it cannot interfere with the subsequent processing.

In an embodiment the first treatment process **303** is a plasma treatment process using a neutral plasma such as argon that will remove the tantalum residue **205** but will not undesirably react with the remaining structure. In an embodiment the first treatment process **303** may be performed with an argon plasma at a temperature of between about 50° C. and about 200° C., such as about 100° C. and at a pressure of between about 10 mTorr and about 100 mTorr, such as about 60 mTorr. Additionally, the first treatment process **303** may be performed for a time of between about 50 s and about 300 s, such as about 150 s, in order to help with the removal of the residue **205** although any suitable process parameters may be utilized.

FIG. 4 illustrates a removal of the second masking layer **301** and a deposition of the first dielectric cap **401** and a second dielectric cap **403**. In an embodiment in which the second masking layer **301** is a photoresist material, the second masking layer **301** may be removed using an ashing process as described above with respect to the removal of the first masking layer **125**. However, any suitable removal process may be utilized.

Once the second masking layer **301** has been removed, the first dielectric cap **401** is deposited to cover the stack of CZT multilayers. In an embodiment the first dielectric cap **401** may be a dielectric material such as silicon oxide, although any suitable dielectric materials, such as silicon nitride, may be utilized. The first dielectric cap **401** may be formed using a deposition process such as chemical vapor deposition, atomic layer deposition, physical vapor deposition, or the like, to a thickness of between about 0.1 μm and about 2 μm , such as about 1 μm . However, any suitable process and thickness may be utilized.

By clearing the tantalum residue **205** from the staircase structure of the CZT multilayers, the tantalum residue **205** is unable to interfere with the deposition process of the first dielectric cap **401**. As such, the deposition of the first dielectric cap **401** (e.g., silicon nitride) may occur with a reduced number of voids, if any, leading to a reduced eddy current as well as an increased inductance level. Additionally, without the interference of the tantalum residue **205**, the silicon nitride will have an increased adhesion, leading to a more structurally sound device.

After the first dielectric cap **401** has been formed, the second dielectric cap **403** may be formed over the first dielectric cap **401**. In an embodiment the second dielectric cap **403** is a different dielectric material from the first dielectric cap **401**. For example, in an embodiment in which the first dielectric cap **401** is silicon oxide, the second dielectric cap **403** is silicon nitride. In another embodiment

in which the first dielectric cap **401** is silicon nitride, the second dielectric cap **403** may be silicon oxide. However, any other suitable dielectric may be utilized. The second dielectric cap **403** may be formed using a deposition process such as chemical vapor deposition, atomic layer deposition, physical vapor deposition, combinations of these, or the like. The second dielectric cap **403** may be formed to a thickness of between about 0.1 μm and about 2 μm , such as about 0.7 μm . However, any suitable deposition process and thickness may be utilized.

Optionally, a third dielectric cap (represented in FIG. 4 by the dashed line **405**) may be formed over the second dielectric cap **403**. In an embodiment the third dielectric cap **405** may be similar to the first dielectric cap **401**, such as by being silicon nitride when the first dielectric cap **401** is silicon nitride or by being silicon oxide when the first dielectric cap **401** is silicon oxide. As such, the combination of the first dielectric cap **401**, the second dielectric cap **403**, and the third dielectric cap **405** form either an Nitride-Oxide-Nitride (NON) dielectric or an Oxide-Nitride-Oxide (ONO) dielectric.

FIG. 5 illustrates a formation of an inductor coil **501** over the dielectric caps. In an embodiment the inductor coil **501** may be part of a redistribution layer that connects the inductor to other portions of the semiconductor device (e.g., the active and passive devices or external connections). In an embodiment the inductor coil **501** may be formed by initially forming a seed layer (not shown) of a titanium copper alloy through a suitable formation process such as CVD or sputtering. A photoresist (also not shown) may then be formed to cover the seed layer, and the photoresist may then be patterned to expose those portions of the seed layer that are located where the inductor coil **501** is desired to be located.

Once the photoresist has been formed and patterned, a conductive material, such as copper, may be formed on the seed layer through a deposition process such as plating. However, while the material and methods discussed are suitable to form the conductive material, these materials are merely exemplary. Any other suitable materials, such as AlCu or Au, and any other suitable processes of formation, such as CVD or PVD, may alternatively be used to form the inductor coil **501**.

Once the conductive material has been formed, the photoresist may be removed through a suitable removal process such as chemical stripping and/or ashing. Additionally, after the removal of the photoresist, those portions of the seed layer that were covered by the photoresist may be removed through, for example, a suitable etch process using the conductive material as a mask.

The inductor coil **501** may be formed to have a fourth width W_4 of between about 10 μm and about 300 μm , such as about 70 μm . Additionally, the inductor coil **501** may be formed to have a fourth thickness T_4 of between about 5 μm and about 20 μm , such as about 14 μm . Also, while only two individual coils of the inductor are illustrated in FIG. 5, any suitable number of coils may be present. However, any suitable dimensions may be utilized.

FIG. 5 also illustrates that once the inductor coil **501** has been formed, a fourth dielectric cap **503** can be formed over the inductor coil **501**. In an embodiment the fourth dielectric cap **503** may be silicon nitride or silicon oxide, and can be either the same material or a different material from the first dielectric cap **401**. As such, in embodiments in which the third dielectric cap **405** is not present, the first dielectric cap **401**, the second dielectric cap **403** and the fourth dielectric cap **503** form a combined Oxide-Nitride-Oxide layer with

the inductor coils **501** sandwiched between parts of the caps, or else may form an Oxide-Nitride-Oxide layer with the inductor coils **501** sandwiched between parts of the caps. The fourth dielectric cap **503** may be formed using a deposition process such as chemical vapor deposition, atomic layer deposition, physical vapor deposition, combinations of these, or the like, to a thickness of between about 0.1 μm and about 2 μm , such as about 1.1 μm . However, any suitable process or thicknesses may be utilized.

FIG. 6A illustrates that, after the fourth dielectric cap **503** has been formed, first openings **601** are formed through the first dielectric cap **401**, the second dielectric cap **403**, the third dielectric cap **405** (if present), and the fourth dielectric cap **503** in order to expose the underlying CZT multilayers on either side of the inductor coil **501**. In an embodiment the first openings **601** may be formed by placing, exposing, and developing a photoresist (not separately illustrated), and then utilizing the developed photoresist as a mask during an anisotropic etching process such as a reactive ion etch. However, any suitable process for forming the first openings **601** may be utilized. The first openings **601** may be formed to have a fifth width W_5 at a top of the first openings **601** of between about 10 μm and about 30 μm , such as about 20 μm , although any suitable dimensions may be utilized.

By using the multiple layers described herein, defects from the formation of the first openings **601** can be reduced or eliminated. In particular, pillar defects that can arise from residual silicon nitride during the etching process, can be eliminated or reduced by using the layers and etching processes described herein. As such, defects can be reduced and a more efficient device can be manufactured.

FIG. 6B illustrates a close up view of the dashed box labeled **603** in FIG. 6A and illustrates a resulting sidewall of the first dielectric cap **401**, the second dielectric cap **403**, and the fourth dielectric cap **503** (without the third dielectric cap **405**). As can be seen, the differing etch selectivities between the different dielectric caps cause a difference in angles between the sidewalls of the first dielectric cap **401**, the second dielectric cap **403**, and the fourth dielectric cap **503**. As such, while the first opening **601** may have an overall sidewall with a second angle θ_2 that has an average value of between about 30 degrees and about 65 degrees, such as about 51.6 or 52 degrees the individual layers may have different angles from each other.

For example, the first dielectric cap **401** may have a third angle θ_3 of between about 10° and about 60°, such as about 40°. Additionally, the second dielectric cap **403** may have a fourth angle θ_4 of between about 20° and about 70°, such as about 60°, while the fourth dielectric cap **503** may have a fifth angle θ_5 of between about 10° and about 60°, such as about 40°. However, any suitable angles may be utilized. Given these differing angles, the second dielectric cap **403** causes the sidewall of the first opening **601** to have a kink profile with the different angles.

FIG. 7 illustrates a formation of a dielectric dome **701** over the inductor coil **501**. In an embodiment the dielectric dome **701** is a dielectric material such as polybenzoxazole (PBO), although any suitable dielectric may be utilized. The dielectric dome **701** may be deposited using a process such as spin-on deposition to a thickness of between about 5 μm and about 25 μm , such as about 21 μm . Once the material of the dielectric dome **701** has been deposited, the material may be patterned into the dielectric dome **701** using, e.g., a masking and etching process, which also re-exposes the CZT multilayers through the first openings **601**.

FIG. 7 additionally illustrates the formation of a sixth CZT multilayer **703** over the inductor coil **501** and through

the first openings **601** in order to make contact with the fifth CZT multilayer **111**. In an embodiment the sixth CZT multilayer **703** may be similar to the first CZT multilayer **103**, such as by being a multilayer comprising a sixth metal layer, a sixth CZT layer, and a sixth OCZT layer. In an embodiment, the sixth metal layer, the sixth CZT layer, and the sixth OCZT layer may be similar to the first metal layer **115**, the first CZT layer **117**, and the first OCZT layer **119**, although they may also be different.

By lowering the pillar defects, the sixth CZT multilayer **703** will have an improved coverage rate as it is being deposited through the first opening **601**. For example, using the processes described herein, the coverage rate of the sixth CZT multilayer **703** can be raised from 58% to greater than 75%, such as 76%, an increase of 18%. Additionally, the inductance (Lac) can be improved from 6.4 nH to 7.0 nH, an increase of 9%.

In accordance with an embodiment, a method of manufacturing a semiconductor device comprising forming a first cobalt-zirconium-tantalum (CZT) layer and a second CZT layer over a semiconductor substrate is provided. The first CZT layer comprises a first metal layer, a first CZT material, and a first oxidized CZT (OCZT) material. A mask is applied over the second CZT layer and the second CZT layer is wet etched to expose a portion of the first CZT layer. The exposed portion of the first CZT layer is treated. A first dielectric material is formed over the second CZT layer, and a first inductor coil is formed over the first dielectric material. A second dielectric material is formed over the first inductor coil, and a third CZT layer is formed through the second dielectric material and in contact with the second CZT layer.

In accordance with another embodiment, a method of manufacturing a semiconductor device comprising forming a plurality of cobalt-zirconium-tantalum (CZT) layers over a substrate, wherein each one of the plurality of CZT layers comprises: a metal layer, an oxidized CZT material layer, and a CZT material between the metal layer and the oxidized CZT material layer, is provided. The plurality of CZT layers are shaped into a staircase pattern, and a first dielectric cap is deposited over the staircase pattern. A second dielectric cap is deposited over the first dielectric cap. An inductor coil is formed over the second dielectric cap, and a third dielectric cap is deposited over the inductor coil. Openings are formed to expose the plurality of CZT layers and a capping CZT layer is deposited over the inductor coil and through the openings.

In accordance with yet another embodiment, a semiconductor device comprising a semiconductor substrate and a plurality of layers over the semiconductor substrate is provided. The plurality of layers has a staircase sidewall and wherein each one of the plurality of layers comprises: a metal layer, a cobalt-zirconium-tantalum (CZT) material over the metal layer, and an oxidized CZT material over the CZT material. A plurality of dielectric layers are over the plurality of layers and an inductor coil is over the plurality of dielectric layers. A capping dielectric is over the inductor coil, and a second CZT material extends over the capping dielectric, through the plurality of dielectric layers, and in contact with at least one of the plurality of layers.

The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments

introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

What is claimed is:

1. A semiconductor device comprising:

a semiconductor substrate;

a plurality of layers over the semiconductor substrate, wherein the plurality of layers has a staircase sidewall and wherein each one of the plurality of layers comprises:

a metal layer;

a cobalt-zirconium-tantalum (CZT) material over the metal layer; and

an oxidized CZT material over the CZT material;

a plurality of dielectric layers over the plurality of layers; an inductor coil over the plurality of dielectric layers;

a capping dielectric over the inductor coil; and

a second CZT material extending over the capping dielectric, through the plurality of dielectric layers, and in contact with at least one of the plurality of layers.

2. The semiconductor device of claim 1, wherein the staircase sidewall has an angle of between about 5 degrees and about 70 degrees.

3. The semiconductor device of claim 1, wherein the metal layer comprises tantalum.

4. The semiconductor device of claim 1, wherein the staircase sidewall has a step length of between about 0.25 μm and about 2 μm .

5. The semiconductor device of claim 1, wherein the staircase sidewall has a step height of between about 0.1 μm and about 0.7 μm .

6. The semiconductor device of claim 1, wherein the second CZT material extends through a first opening, the first opening extending through the capping dielectric and the plurality of dielectric layers, wherein the first opening has a first sidewall with a kink profile.

7. The semiconductor device of claim 6, wherein the first sidewall has a first portion at a first angle of between 10° and about 60°, a second portion at a second angle different from the first angle and between about 20° and about 70°, and a third portion at a third angle different from the second angle and between about 10° and about 60°.

8. A semiconductor device comprising:

a first cobalt-zirconium-tantalum (CZT) layer and a second CZT layer over a semiconductor substrate, wherein the first CZT layer comprises:

a first metal layer;

a first CZT material; and

a first oxidized CZT (OCZT) material;

a first dielectric material over the second CZT layer;

a first inductor coil over the first dielectric material;

a second dielectric material over the first inductor coil; and

a third CZT layer extending through the second dielectric material and in contact with the second CZT layer.

9. The semiconductor device of claim 8, wherein the first metal layer has a first thickness of between about 10 Å and about 100 Å.

10. The semiconductor device of claim 9, wherein the first CZT material has a second thickness of between about 100 Å and about 5000 Å.

11. The semiconductor device of claim 10, wherein the first OCZT material has a third thickness of between about 20 Å and about 5000 Å.

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12. The semiconductor device of claim **9**, wherein the first CZT material has a second thickness of between about 1 and about 10 times the first thickness.

13. The semiconductor device of claim **8**, wherein the first CZT layer has a thickness of between about 0.1 μm and about 0.7 μm .

14. The semiconductor device of claim **8**, wherein the second CZT layer overlies some but not all of the first CZT layer.

15. A semiconductor device comprising:

a plurality of cobalt-zirconium-tantalum (CZT) layers over a substrate, and having a sidewall with a staircase pattern, wherein each one of the plurality of CZT layers comprises:

a metal layer;

an oxidized CZT material layer; and

a CZT material between the metal layer and the oxidized CZT material layer;

a first dielectric cap formed conformally over the staircase pattern;

a second dielectric cap over the first dielectric cap;

an inductor coil over the second dielectric cap;

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a third dielectric cap over the inductor coil; and
a capping CZT layer over the inductor coil and through the third dielectric cap.

16. The semiconductor device of claim **15**, wherein the plurality of CZT layers has a thickness of between about 2 μm and about 10 μm .

17. The semiconductor device of claim **15**, wherein the first dielectric cap, the second dielectric cap, and the third dielectric cap have a combined angle of between about 30° and about 65°.

18. The semiconductor device of claim **17**, wherein the second dielectric cap has a kink profile.

19. The semiconductor device of claim **15**, wherein the first dielectric cap comprises an oxide material, the second dielectric cap comprises a nitride material, and the third dielectric cap comprises an oxide material.

20. The semiconductor device of claim **15**, wherein the first dielectric cap is a nitride material, the second dielectric cap comprises an oxide material, and the third dielectric cap comprises a nitride material.

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